

MOSFETs Silicon 430V N-Channel MOS
■ Applications

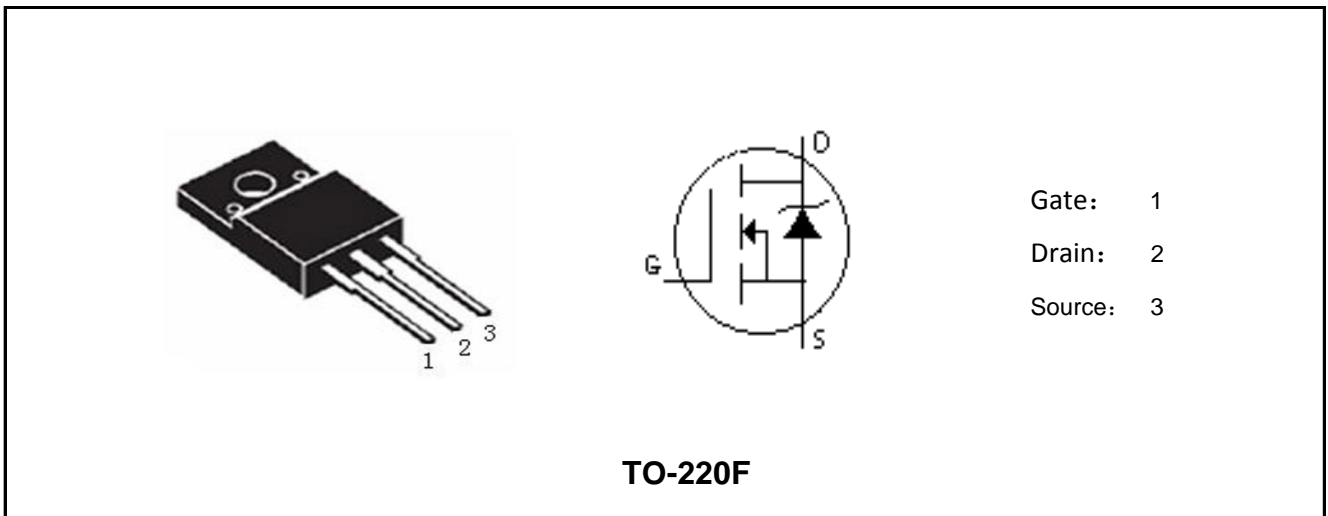
- Power factor correction (PFC)
- Switched mode power supplies(SMPS)
- Uninterruptible Power Supply (UPS)

■ Features

- Low $R_{DS(ON)}$
- Ultra Low Gate Charge
- RoHS Compliant
- 100% UIS and RG Tested

■ Product Summary

V_{DS}	430	V
I_D	11	A
$R_{DS(ON)}, Typ @10V$	0.47	Ω
Q_g	20	nC



Marking	Package	Packaging	Min. package quantity
MFIRF11N45	TO-220F	Tube	1000



■ Absolute Maximum Ratings (Tc=25°C unless otherwise noted)

Parameter	Symbol	Ratings	Unit
Drain-Source Voltage	V_{DS}	430	V
Gate-Source Voltage	V_{GS}	±30	V
Continuous Drain Current Tc=25°C (Note 1)	I_D	11	A
Continuous Drain Current Tc=100°C (Note 1)		6.8	
Drain Current-Pulsed (Note 1)	I_{DM}	44	A
Total Dissipation	P_D	50	W
Junction Temperature	T_j	150	°C
Storage Temperature	T_{stg}	-55-150	°C
Single Pulse Avalanche Energy (Note 2)	E_{AS}	450	mJ

Note: Using continuously under heavy loads (e.g. the application of high temperature/current/voltage and the significant change in temperature, etc.) may cause this product to decrease in the reliability significantly even if the operating conditions (i.e. operating temperature/current/voltage, etc.) are within the absolute maximum ratings.

■ Thermal Characteristics

Parameter	Symbol	Max	Unit
Maximum Junction-to-Case	$R_{\theta JC}$	2.5	°C/W
Maximum Junction-to-Ambient	$R_{\theta JA}$	80	°C/W

Note 1: Ensure that the channel temperature does not exceed 150°C.

Note 2: $V_{DD}=50V$, $T_{ch}=25^\circ C$ (initial), $I_{AS}=11A$, $R_g=25\Omega$.

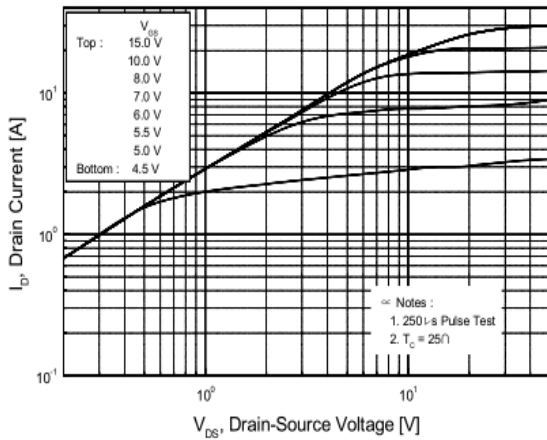
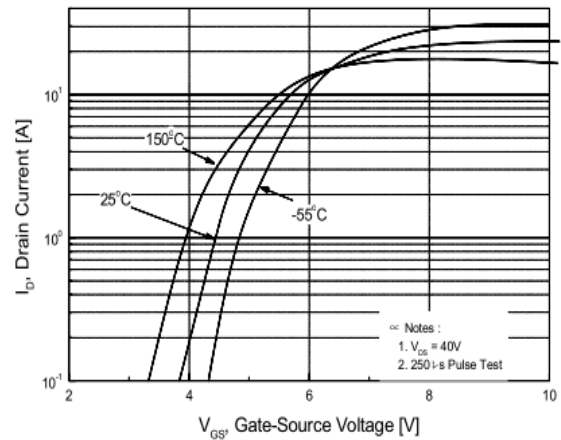
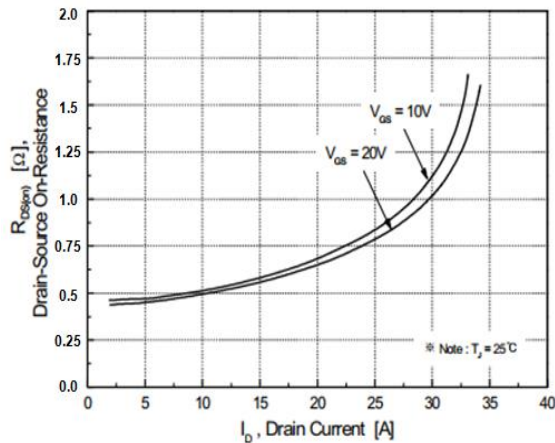
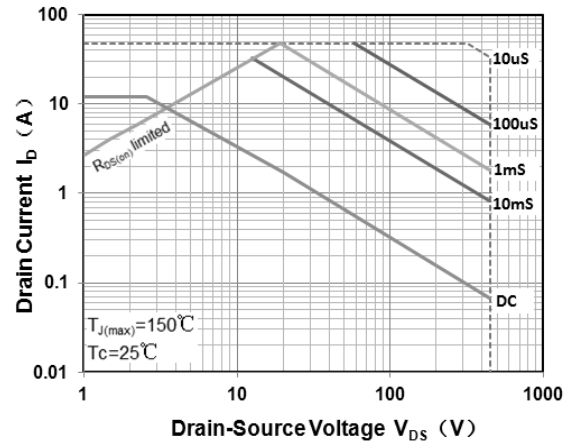
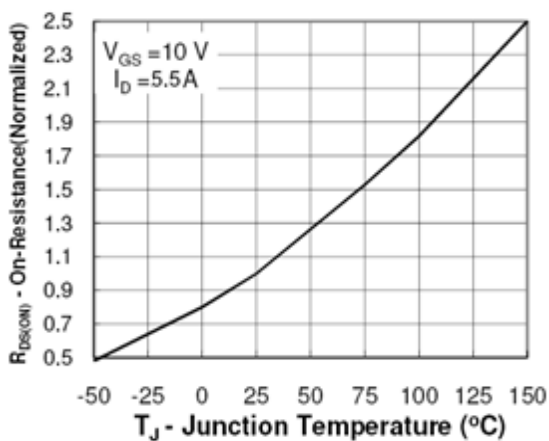
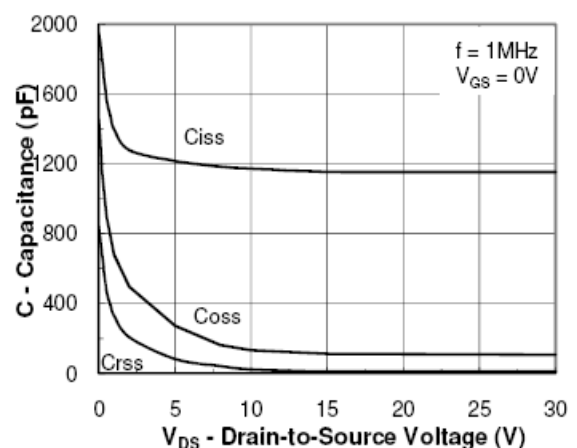
Note: This transistor is sensitive to electrostatic discharge and should be handled with care.

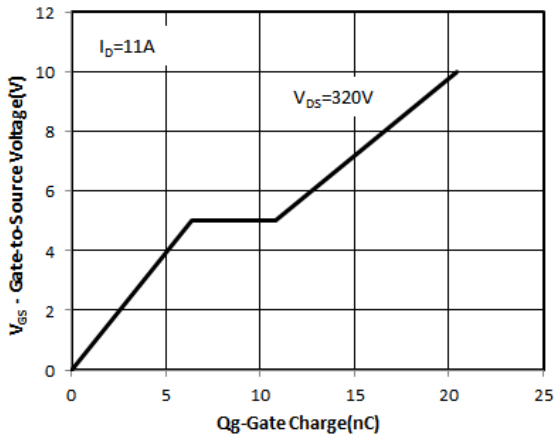


■ Electrical Characteristics (Tc=25°C unless otherwise noted)

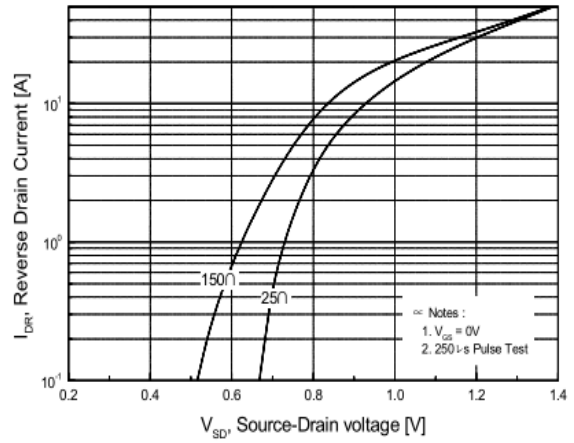
Parameter	Symbol	Test Condition	Min	Typ	Max	Unit
Static Parameters						
Drain-Source Breakdown Voltage	BV_{DSS}	$V_{GS}=0V, I_D=250\mu A$	430	-	-	V
Drain-Source Leakage Current	I_{DSS}	$V_{DS}=430V, V_{GS}=0V$	-	-	1	μA
Gate-Body Leakage Current	I_{GSS}	$V_{GS}=\pm 30V, V_{DS}=0V$	-	-	± 100	nA
Gate Threshold Voltage	$V_{GS(TH)}$	$V_{GS}=V_{DS}, I_D=250\mu A$	2	3	4	V
Drain-Source On Resistance	$R_{DS(ON)}$	$V_{GS}=10V, I_D=5.5A$	-	0.47	0.5	Ω
Dynamic Characteristics						
Input Capacitance	C_{iss}	$V_{DS}=25V, V_{GS}=0V,$ $f=1.0MHz$	-	1120	-	pF
Output Capacitance	C_{oss}		-	118	-	pF
Reverse Transfer Capacitance	C_{rss}		-	10	-	pF
Gate Resistance	R_g	$V_{DS}=0V, V_{GS}=0V,$ $f=1.0MHz$	-	2	-	Ω
Switching Parameters						
Turn-On Delay Time	$t_{d(on)}$	$V_{DS}=250V, I_D=11A,$ $V_{GS}=10V, R_G=25\Omega$	-	32	-	ns
Turn-On Rise Time	t_r		-	28	-	ns
Turn-Off Delay Time	$t_{d(off)}$		-	90	-	ns
Turn-Off Rise Time	t_f		-	50	-	ns
Total Gate Charge	Q_g	$V_{DS}=320V, I_D=11A,$ $V_{GS}=10V$	-	20	-	nC
Gate-Source Charge	Q_{gs}		-	6.5	-	nC
Gate-Drain Charge	Q_{gd}		-	4.5	-	nC
Source-Drain Characteristics						
Max. Diode Forward Current	I_S		-	-	11	A
Max. Pulsed Forward Current	I_{SM}		-	-	44	A
Diode Forward Voltage	V_{SD}	$V_{GS}=0V, I_S=11A$	-	0.86	1.5	V
Reverse Recovery Time	t_{rr}	$V_R=320V, I_F=11A,$ $di/dt=100A/\mu s$	-	320	-	ns
Reverse Recovery Charge	Q_{rr}		-	3.2	-	μC



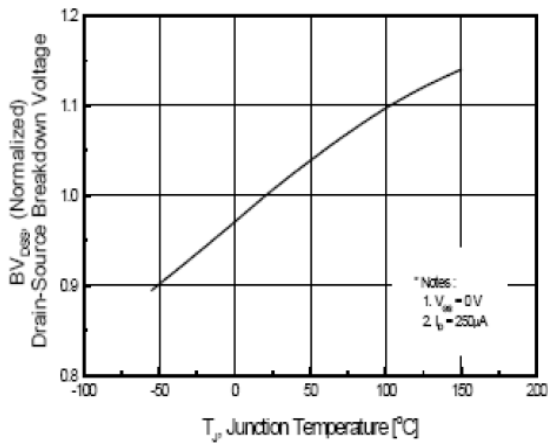
■ Characteristics Curves

Output Characteristics

Transfer Characteristics

On Resistance Vs Drain Current

Safe Operating Area

Rdson-Junction Temperature

Capacitance

Gate Charge Waveform



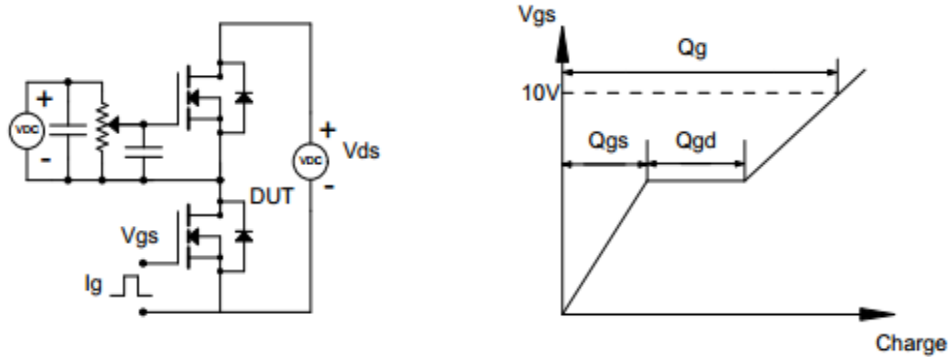
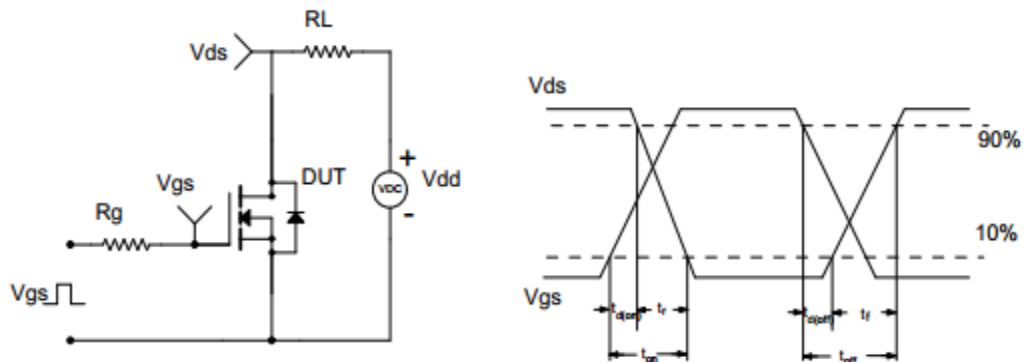
Source-Drain Diode Forward Voltage



Breakdown Voltage Vs Junction Temperature

Note : The above characteristics curves are presented for reference only and not guaranteed by production test, unless otherwise noted.



■ Test Circuit & Waveform
Gate Charge Test Circuit & Waveform

Resistive Switching Test Circuit & Waveform

Unclamped Inductive Switching (UIS) Test Circuit & Waveform
